

NCE40P05Y

NCE P-Channel Enhancement Mode Power MOSFET

Description

The NCE40P05Y uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

V_{DS} =-40V,I_D =-5.3A

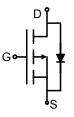
 $R_{DS(ON)}$ <85m Ω @ V_{GS} =-10V

 $R_{DS(ON)}$ <120m Ω @ V_{GS} =-4.5V

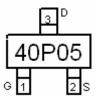
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

Application

- Power switching application
- Hard switched and high frequency circuits
- DC-DC converter



Schematic diagram



Marking and pin assignment



SOT-23-3L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
40P05	NCE40P05Y	SOT23-3L	Ø330mm	12mm	2500 units

Absolute Maximum Ratings (T_A=25 °C unless otherwise noted)

Absolute maximum rutings (14-20 cumess culerwise noted)					
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V _{DS}	-40	V		
Gate-Source Voltage	V _{GS}	±20	V		
Drain Current-Continuous	I _D	-5.3	А		
Drain Current-Continuous(T _C =100 °C)	I _D (100℃)	-3.65	А		
Pulsed Drain Current	I _{DM}	-20	А		
Maximum Power Dissipation	P _D	2.0	W		
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	$^{\circ}\mathbb{C}$		

Thermal Characteristic

		Î	
Thermal Resistance ,Junction-to-Ambient(Note 2)	$R_{ heta JA}$	62.5	°C/W

Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
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Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-40	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-40V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)	·					
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =-250μA	-1.0	-1.9	-3.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-5A	-	73	85	mΩ
Drain-Gource On-Gtate Resistance	TVDS(ON)	V_{GS} =-4.5 V , I_D =-4 A	-	98	120	mΩ
Forward Transconductance	g FS	V _{DS} =-15V,I _D =-3.1A	10	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}	\/ 00\/\/ 0\/	-	600	-	PF
Output Capacitance	C _{oss}	V_{DS} =-20V, V_{GS} =0V, F=1.0MHz	-	90	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.UIVIHZ	-	70	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	9	-	nS
Turn-on Rise Time	t _r	V_{DD} =-20V, , R_L =2 Ω	-	8	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =-10 V , R_{GEN} =3 Ω	-	28	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Qg	\/ 00\/ L 5A	-	14	-	nC
Gate-Source Charge	Q _{gs}	V_{DS} =-20V, I_{D} =-5A,	-	2.9	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} =-10V	-	3.8	-	nC
Drain-Source Diode Characteristics			•			
Diode Forward Voltage (Note 3)	V _{SD}	V_{GS} =0 V , I_{S} =-5 A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	-5.3	Α

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- **3.** Pulse Test: Pulse Width ≤ 300μ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production

Pb Free Product

NCE40P05Y

Typical Electrical and Thermal Characteristics

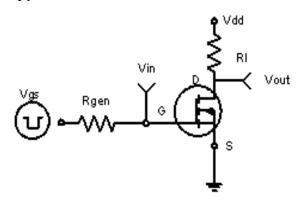


Figure 1:Switching Test Circuit

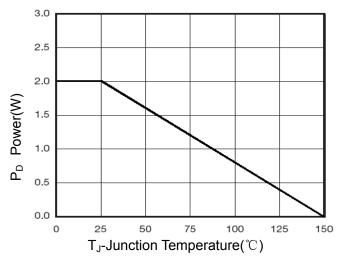
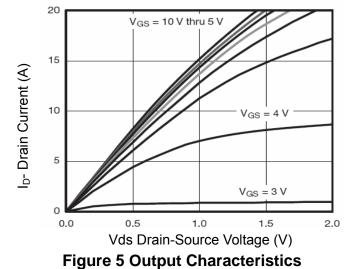


Figure 3 Power Dissipation



 $\mathbf{t}_{\text{d(on)}}$ $t_{d(off)}$ V_{OUT} **INVERTED** V_{IN} 50% 10% **PULSE WIDTH**

Figure 2:Switching Waveforms

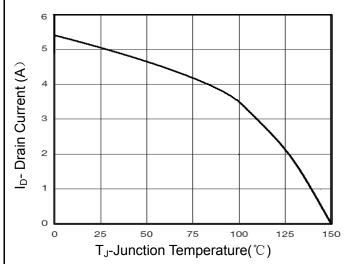


Figure 4 Drain Current

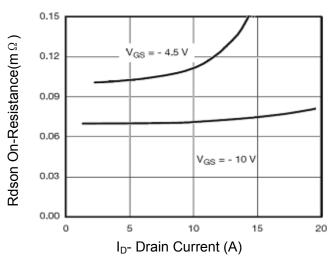


Figure 6 Drain-Source On-Resistance



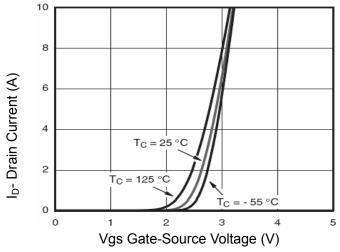


Figure 7 Transfer Characteristics

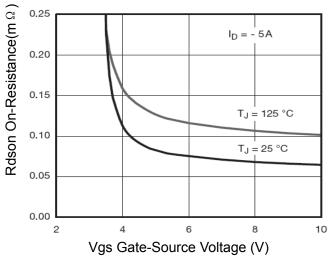


Figure 9 Rdson vs Vgs

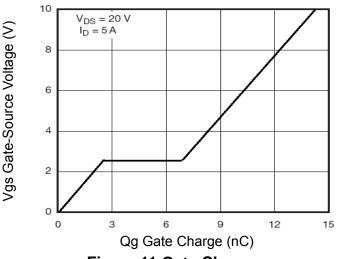


Figure 11 Gate Charge

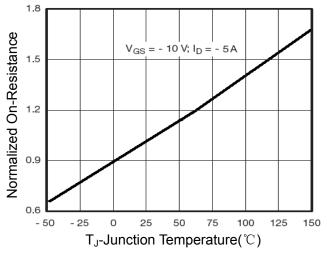


Figure 8 Drain-Source On-Resistance

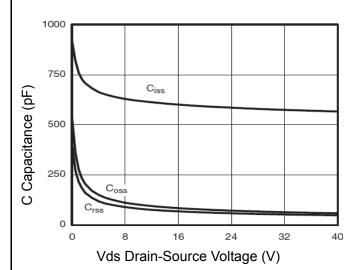


Figure 10 Capacitance vs Vds

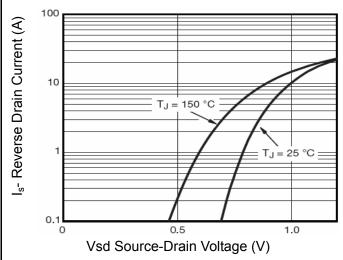


Figure 12 Source- Drain Diode Forward



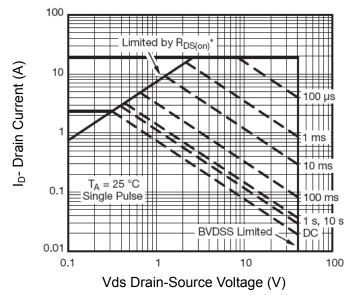


Figure 13 Safe Operation Area

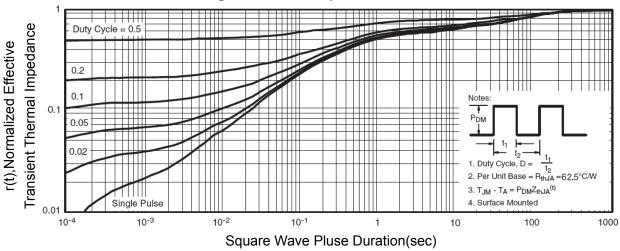
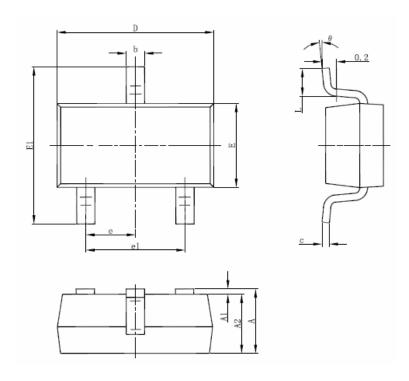


Figure 14 Normalized Maximum Transient Thermal Impedance



SOT-23-3L Package Information



Symbol	Dimensions Ir	Millimeters	Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	1.050	1.250	0.041	0.049	
A1	0.000	0.100	0.000	0.004	
A2	1.050	1.150	0.041	0.045	
b	0.300	0.500	0.012	0.020	
С	0.100	0.200	0.004	0.008	
D	2.820	3.020	0.111	0.119	
E	1.500	1.700	0.059	0.067	
E1	2.650	2.950	0.104	0.116	
е	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079	
L	0.300	0.600	0.012	0.024	
θ	0°	8°	0°	8°	

Notes

- 1. All dimensions are in millimeters.
- 2. Tolerance ±0.10mm (4 mil) unless otherwise specified
- 3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- 4. Dimension L is measured in gauge plane.
- $5. \ Controlling \ dimension \ is \ millimeter, \ converted \ inch \ dimensions \ are \ not \ necessarily \ exact.$



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